Si Micro-Holes

1 µm in diameter holes with 1.5 um thick SiO2 as etch mask

Bosch Process

Dep. Step
• Pressure: 15 mTorr
• C4F8: 120 sccm
• Coil power: 600W
• Platen power: 0W
• Time: 5 second

Etch Step
• Pressure: 15 mTorr
• SF6: 130 sccm
• O2: 13 sccm
• Coil power: 600W
• Platen power: 12W
• Time: 5 second

Results
• Etch rate: 0.4 µm/min
• Profile: 88°
• Selectivity: 20:1